Electronic Supplementary Material (ESI) for Inorganic Chemistry Frontiers.

Defect Control in $Ca_{1-\delta}Ce_{\delta}Ag_{1-\delta}Sb$ ($\delta \approx 0.15$) Through Nb Doping

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Supporting information

Contents

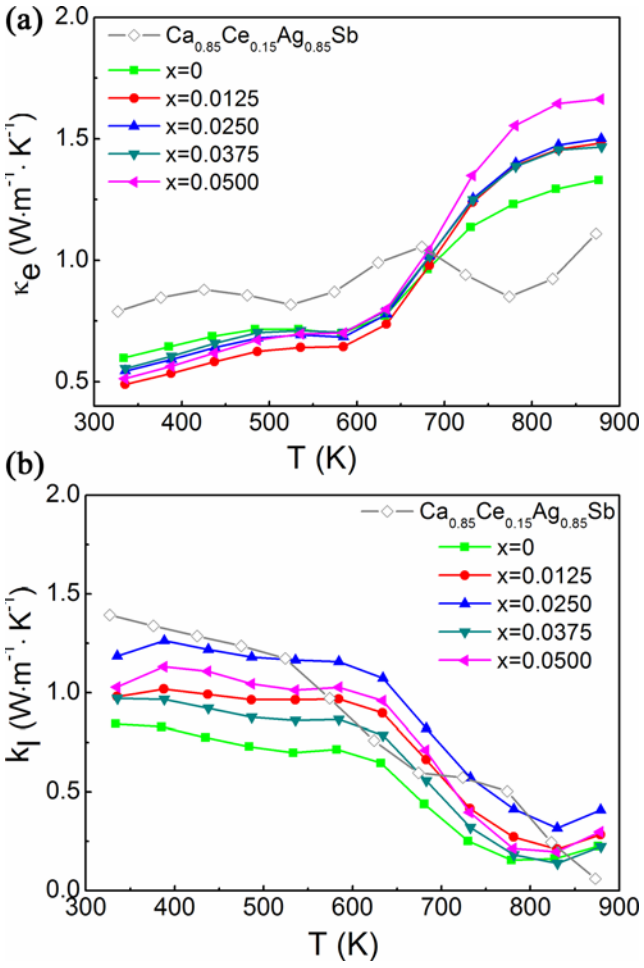

Figure S1. The electronic (κ_e) and lattice (κ_l) contributions of thermal conductivity for $Ca_{0.725+x}Nb_{0.1-x}Ce_{0.15}AgSb$ ($x \leq 0.05$) and $Ca_{0.85}Ce_{0.15}Ag_{0.85}Sb$ compounds.

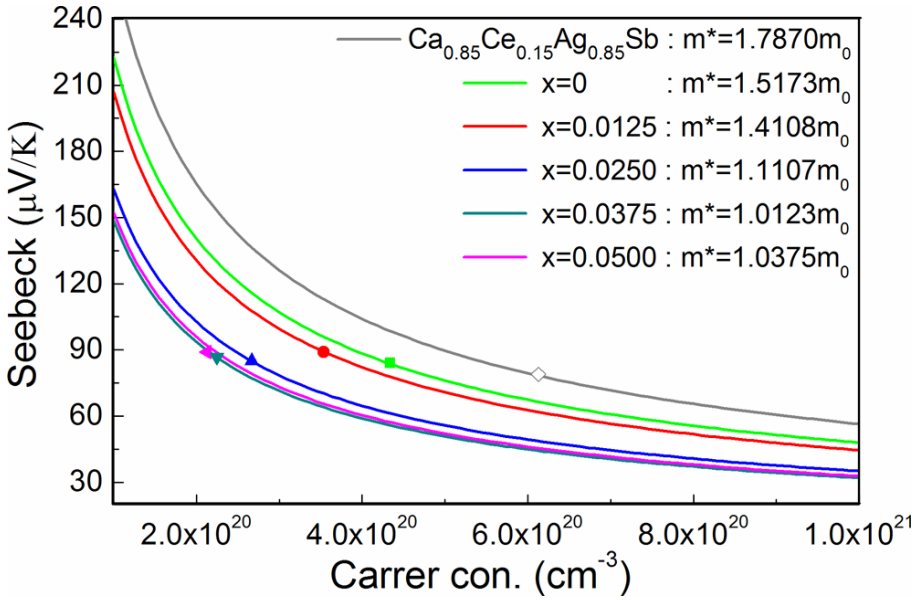

Figure S2. Seebeck Pisarenko plot for $Ca_{0.725+x}Nb_{0.1-x}Ce_{0.15}AgSb$ ($x \leq 0.05$) and $Ca_{0.85}Ce_{0.15}Ag_{0.85}Sb$ compounds. Experimental data are shown as scattered dots in different colors and the curves were calculated based on the SPB (Single Parabolic Band) model.